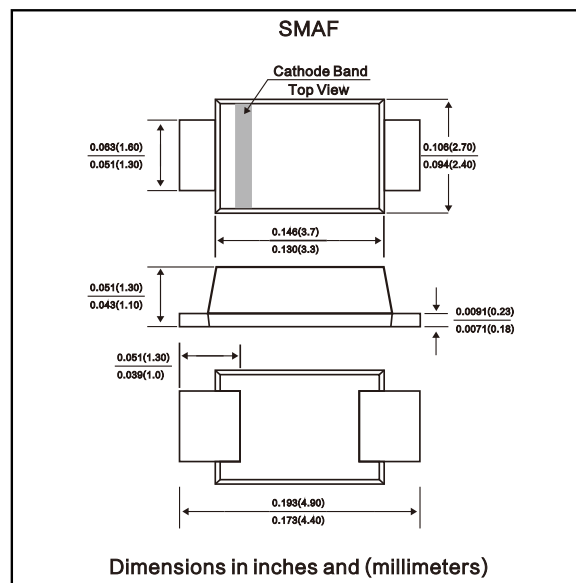


FEATURES

- Metal silicon junction, majority carrier conduction
- For surface mounted applications
- Low power loss, high efficiency
- High forward surge current capability
- For use in low voltage, high frequency inverters, free wheeling, and polarity protection applications

MECHANICAL DATA

- Case: SMAF
- Terminals: Solderable per MIL-STD-750, Method 2026
- Approx. Weight: 27mg / 0.00095oz



Absolute Maximum Ratings and Electrical characteristics

Ratings at 25 °C ambient temperature unless otherwise specified. Single phase, half wave, 60Hz resistive or inductive load, for capacitive load, derate by 20 %

Parameter	Symbols	SS52F	SS54F	SS56F	SS58F	SS510F	SS512F	SS515F	SS520F	Units
Maximum Repetitive Peak Reverse Voltage	V_{RRM}	20	40	60	80	100	120	150	200	V
Maximum RMS voltage	V_{RMS}	14	28	42	56	70	84	105	140	V
Maximum DC Blocking Voltage	V_{DC}	20	40	60	80	100	120	150	200	V
Maximum Average Forward Rectified Current	$I_{F(AV)}$	5.0								A
Peak Forward Surge Current, 8.3ms Single Half Sine-wave Superimposed on Rated Load (JEDEC method)	I_{FSM}	175				150				A
Max Instantaneous Forward Voltage at 5 A	V_F	0.45	0.55	0.70		0.85				V
Maximum DC Reverse Current $T_a = 25^\circ\text{C}$ at Rated DC Reverse Voltage $T_a = 100^\circ\text{C}$	I_R					1.0 50				mA
Typical Junction Capacitance ⁽¹⁾	C_j	700			500					pF
Typical Thermal Resistance ⁽²⁾	$R_{\theta JA}$					50				°C/W
Operating Junction Temperature Range	T_j					-55 ~ +150				°C
Storage Temperature Range	T_{stg}					-55 ~ +150				°C

(1) Measured at 1 MHz and applied reverse voltage of 4 V D.C

(2) P.C.B. mounted with 2.0" X 2.0" (5 X 5 cm) copper pad areas.

Fig.1 Forward Current Derating Curve

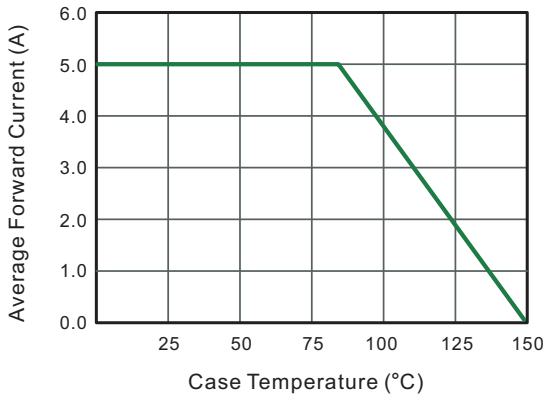


Fig.2 Typical Reverse Characteristics

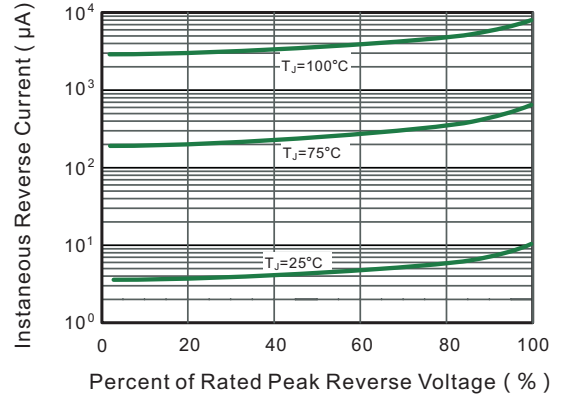


Fig.3 Typical Forward Characteristic

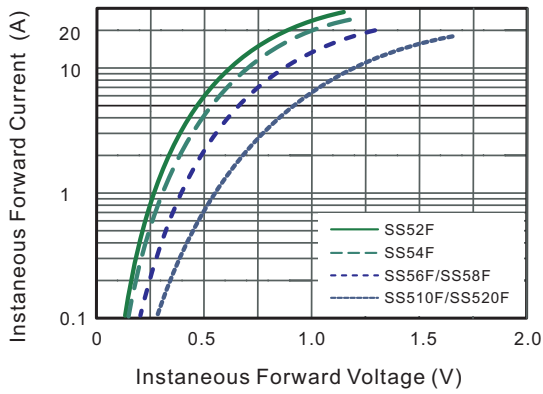


Fig.4 Typical Junction Capacitance

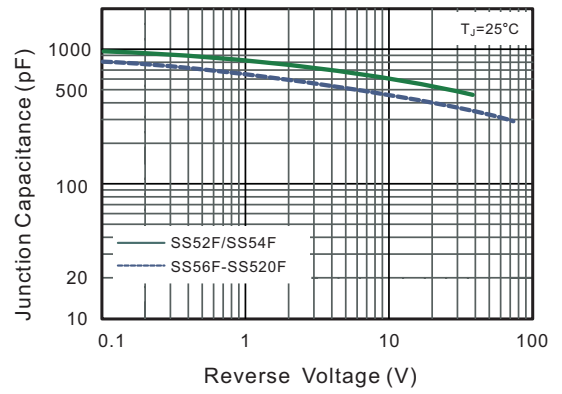


Fig.5 Maximum Non-Repetitive Peak Forward Surge Current

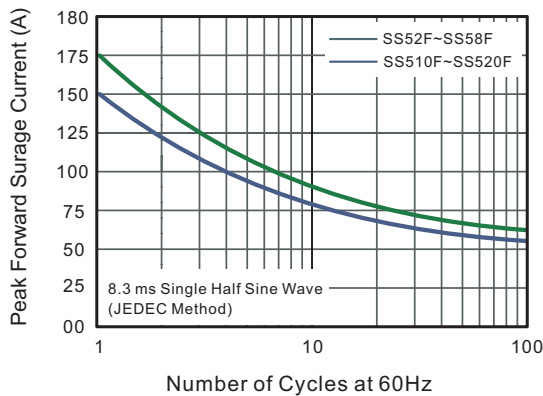


Fig.6- Typical Transient Thermal Impedance

